

APPENDIX

CLAIMS:

1-10. (Cancelled).

11. A polishing pad used for polishing a semiconductor wafer while supplying a polishing agent onto the polishing pad in a mirror polishing process, wherein the polishing pad comprises a base layer formed of nonwoven fabric and a porous surface layer formed of foamed polyurethane, and a content of zinc oxide (ZnO) included in the polishing pad is 200ppm or less at the ratio of zinc weight relative to the weight of the polishing pad.

12. A polishing pad used for polishing a semiconductor wafer while supplying a polishing agent onto the polishing pad in a finish polishing process, wherein the polishing pad comprises a base layer formed of nonwoven fabric and a porous surface layer formed of foamed polyurethane, and a content of zinc oxide (ZnO) included in the polishing pad is 100ppm or less at the ratio of zinc weight relative to the weight of the polishing pad.

13. A polishing pad used for polishing a semiconductor wafer while supplying a polishing agent onto the polishing pad in a finish polishing process, wherein the polishing pad comprises a base layer formed of nonwoven fabric and a porous surface layer formed of foamed polyurethane, and the polishing pad does not include zinc oxide (ZnO).

14-16. (Cancelled).

17. The polishing pad used for polishing a semiconductor wafer according to Claim 11, wherein a content of zinc oxide (ZnO) in the porous surface layer is 100ppm or less at the ratio of zinc weight relative to the weight of the porous surface layer.

18. The polishing pad used for polishing a semiconductor wafer according to Claim 12, wherein a content of zinc oxide (ZnO) in the porous surface layer is 100ppm or less at the ratio of zinc weight relative to the weight of the porous surface layer.

19. (Cancelled).

20. A polishing pad used for polishing a semiconductor wafer while supplying a polishing agent onto the polishing pad in a mirror polishing process, wherein it comprises a base layer formed of nonwoven fabric and a porous surface layer formed of foamed polyurethane, and a content of zinc oxide (ZnO) included in the porous surface layer is 100ppm or less at the ratio of zinc weight relative to the weight of the porous surface layer.

21. The polishing pad for polishing a semiconductor wafer according to Claim 20, wherein the porous surface layer does not include zinc oxide (ZnO).

22-26. (Canceled).

27. A method for polishing a semiconductor wafer, comprising performing polishing of the semiconductor wafer with the polishing pad of Claim 11 while supplying a polishing agent onto the polishing pad.

28. A method for polishing a semiconductor wafer, comprising performing polishing of the semiconductor wafer with the polishing pad of Claim 12 while supplying a polishing agent onto the polishing pad.

29. A method for polishing a semiconductor wafer, comprising performing polishing of the semiconductor wafer with the polishing pad of Claim 13 while supplying a polishing agent onto the polishing pad.

30. A method for polishing a semiconductor wafer, comprising performing polishing of the semiconductor wafer with the polishing pad of Claim 20 while supplying a polishing agent onto the polishing pad.

31. (Canceled).